

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	15	nevin near william.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	26	mccann near paul.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	1	(buried near cavity) near35 ((second) near (wafer or substrate))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	848	(buried) near35 ((second) near (wafer or substrate))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	86	(buried) near35 (bond\$3) near35 ((second) near (wafer or substrate))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L6	744	(recess\$3 or cavity or opening) near35 (bond\$3) near35 ((second) near (wafer or substrate))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L7	442	(recess\$3 or cavity or opening) near35 (bond\$3) near35 ((second) near (wafer or substrate)) near25 ((first) near (wafer or substrate))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L8	244	(aperture or hole\$1) near35 (bond\$3) near35 ((second) near (wafer or substrate)) near25 ((first) near (wafer or substrate))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	357	(via) near35 (bond\$3) near35 ((second) near (wafer or substrate)) near25 ((first) near (wafer or substrate))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L10	107463	(etch\$5) near15 ((hole or cavit\$3 or opening or aperture\$1))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L11	612	((etch\$5) near15 ((hole or cavit\$3 or opening or aperture\$1))) near15 ((second) near (wafer or substrate))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L12	901	((etch\$5) near15 ((hole or cavit\$3 or opening or aperture\$1))) near15 ((first) near (wafer or substrate))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	197	((etch\$5) near15 ((hole or cavit\$3 or opening or aperture\$1))) near15 ((first) near (wafer or substrate))) near25 ((second) near (wafer or substrate))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
14	BRS	L14	2	((etch\$5) near15 ((hole or cavit\$3 or opening or aperture\$1))) near15 (after) near15 ((first) near (wafer or substrate))) near25 ((second) near (wafer or substrate))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	U	1	Document ID	Title
1			US 20040067604 A1	Wafer level packaging technique for microdevices
2			US 20030155639 A1	Solid-state imaging device, method for producing same, and mask
3			US 20030026522 A1	Optical device, in particular optical switching device with improved stability of the bubbles and reduced insertion losses
4			US 20030024317 A1	Ultrasonic transducer wafer having variable acoustic impedance
5			US 20020027576 A1	Ink-jet head, method of producing the same, and ink-jet printing system including the same
6			US 20010027605 A1	Method for producing printed wiring board
7			US 6873034 B2	Solid-state imaging device, method for producing same, and mask
8			US 6808956 B2	Thin micromachined structures
9			US 6804424 B2	Optical device, in particular optical switching device with improved stability of the bubbles and reduced insertion losses

	U	1	Document ID	Title
10			US 6758094 B2	Ultrasonic transducer wafer having variable acoustic impedance
11			US 6682963 B2	Semiconductor device and manufacturing method thereof
12			US 6625880 B2	Method for producing printed wiring board
13			US 6568794 B2	Ink-jet head, method of producing the same, and ink-jet printing system including the same
14			US 5981981 A	Semiconductor device including a bipolar structure
15			US 5883420 A	Sensor device having a pathway and a sealed cavity
16			US 5645684 A	Multilayer high vertical aspect ratio thin film structures

	U	1	Document ID	Title
17			US 5496616 A	Optical element for correcting non-uniform diffraction efficiency in a binary diffractive optical element
18			US 5204690 A	Ink jet printhead having intergral silicon filter
19			JP 2001264723 A	OPTOELECTRONIC DEVICE, ITS MANUFACTURING METHOD AND PROJECTION TYPE DISPLAY DEVICE
20	X		JP 2001063072 A	PRODUCTION OF INK JET HEAD
21	X		JP 2000141300 A	MANUFACTURING OF MICROSTRUCTURE HAVING INTERNAL CAVITY